

# MMBT3906T

Rev.E Mar.-2016

## 描述 / Descriptions

SOT-89 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a SOT-89 Plastic Package.

## 特征 / Features

高  $h_{FE}$  , 低  $V_{CE(sat)}$  。

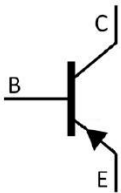
High DC Current Gain, Low Collector to Emitter Saturation Voltage.

## 用途 / Applications

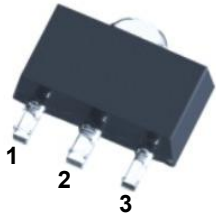
用于普通放大及开关。

General purpose amplifier and switching.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : Base

PIN 2 : Collector

PIN 3 : Emitter

## 印章代码 / Marking

$h_{FE}$ Range	100~300
Marking	H2A * *

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	$V_{CBO}$	-40	V
Collector to Emitter Voltage	$V_{CEO}$	-40	V
Emitter to Base Voltage	$V_{EBO}$	-5.0	V
Collector Current - Continuous	$I_C$	-200	mA
Collector Power Dissipation	$P_C$	450	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C

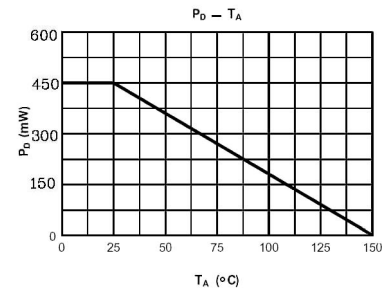
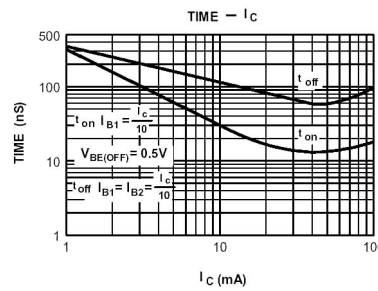
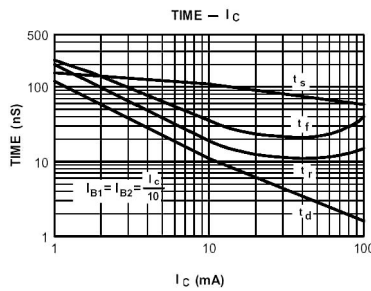
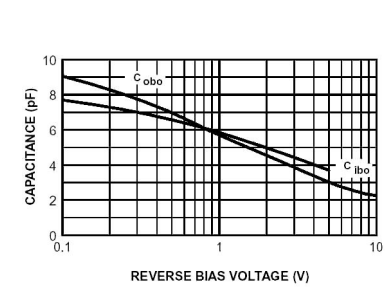
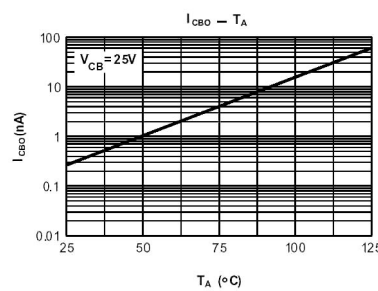
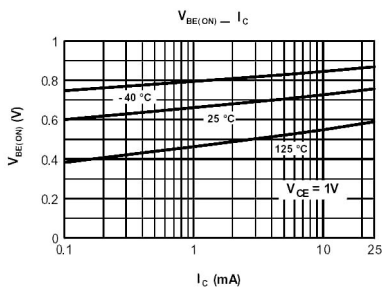
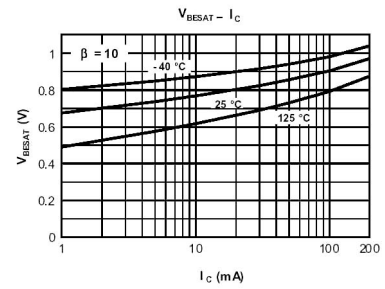
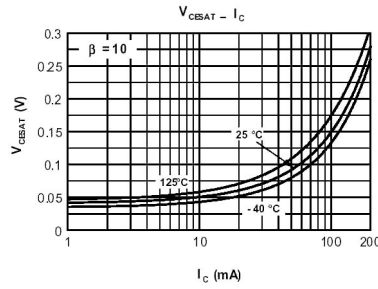
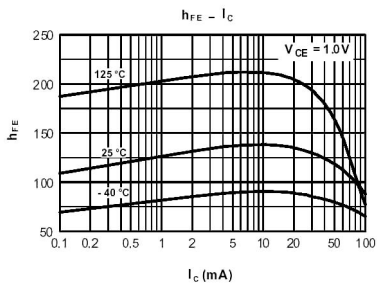
**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=-10mA$ $I_E=0$	-40			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=-1.0mA$ $I_B=0$	-40			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=-10\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=-30V$ $I_E=0$			-0.05	$\mu A$
Emitter Base Cut-Off Current	$I_{EBO}$	$V_{EB}=-3.0V$ $I_C=0$			-0.05	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-10mA$	100		300	
	$h_{FE(2)}$	$V_{CE}=-1.0V$ $I_C=-100mA$	30			
	$h_{FE(3)}$	$V_{CE}=-1.0V$ $I_C=-50mA$	60			
	$h_{FE(4)}$	$V_{CE}=-1.0V$ $I_C=-1.0mA$	80			
	$h_{FE(5)}$	$V_{CE}=-1.0V$ $I_C=-0.1mA$	60			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$			-0.25	V
	$V_{CE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$			-0.4	V
Emitter to Base Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$	-0.65		-0.85	V
	$V_{BE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$			-0.95	V

## 电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Transition Frequency	$f_T$	$I_C=-10mA$ $V_{CE}=-20V$ $f=100MHz$	250			MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-5.0V$ $f=1.0MHz$			4.5	pF
Storage Time	$t_{stg}$	$V_{CC}=-3.0V$ $I_C=-10mA$ $I_{B1}=-I_{B2}=-1.0mA$			225	ns
Fall Time	$t_f$	$V_{CC}=-3.0V$ $I_C=-10mA$ $I_{B1}=-I_{B2}=-1.0mA$			75	ns
Delay Time	$t_d$	$V_{CC}=-3.0V$ $V_{BE}=-0.5V$ $I_C=-10mA$ $I_{B1}=-1.0mA$			35	ns
Rise Time	$t_r$	$V_{CC}=-3.0V$ $V_{BE}=-0.5V$ $I_C=-10mA$ $I_{B1}=-1.0mA$			35	ns
Input Capacitance	$C_{ib}$	$V_{EB}=-0.5V$ $f=1.0MHz$			10	pF

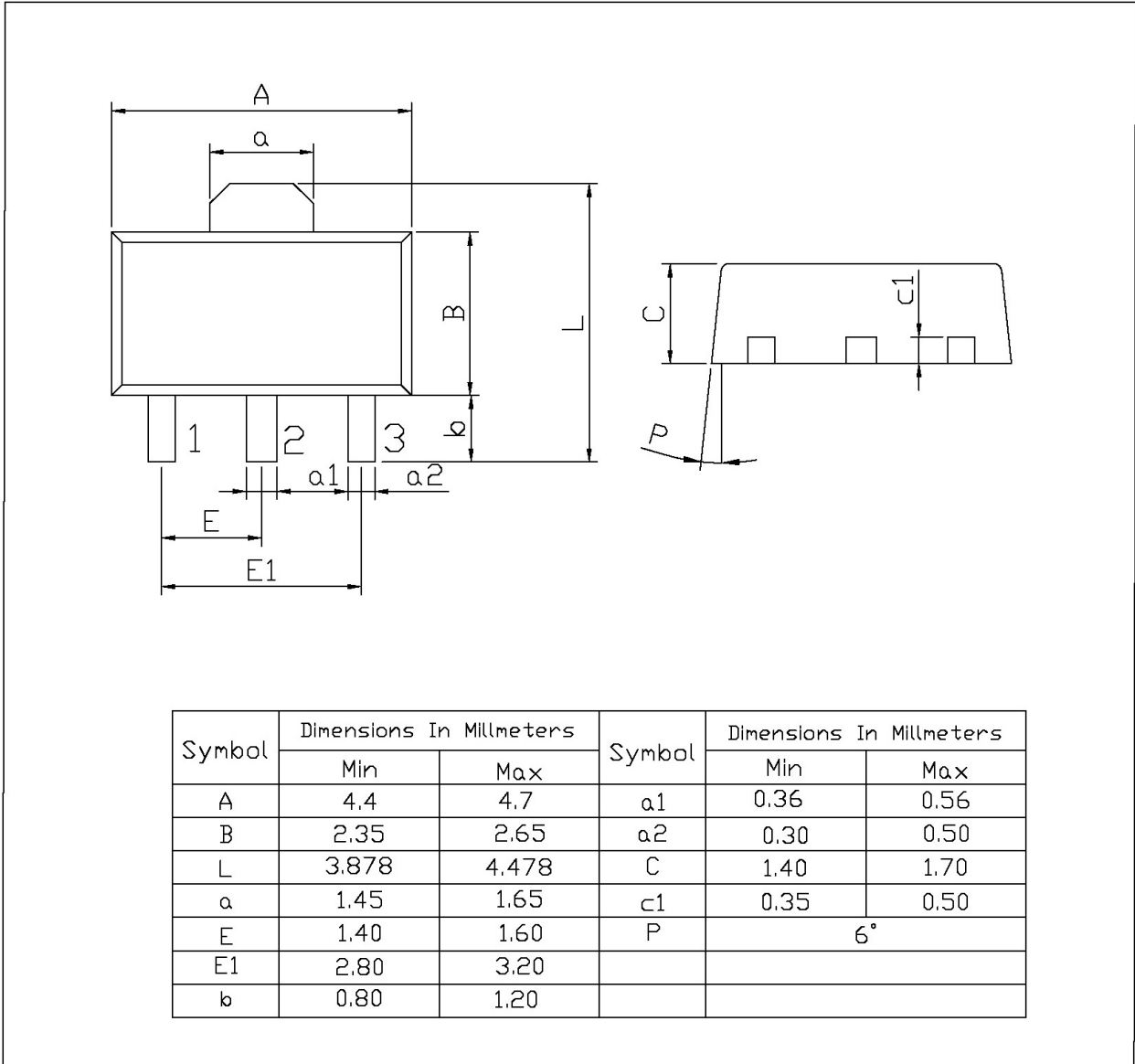
电参数曲线图 / Electrical Characteristic Curve



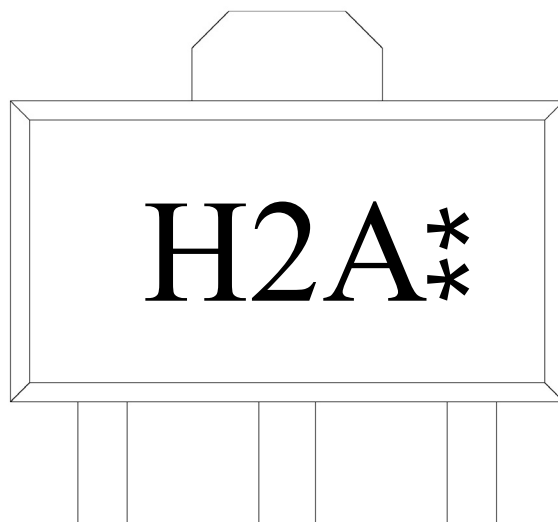
外形尺寸图 / Package Dimensions

SOT-89

单位: mm



印章说明 / Marking Instructions



说明：

H： 为公司代码

2A： 为型号代码

\*\*： 为生产批号代码，随生产批号变化。

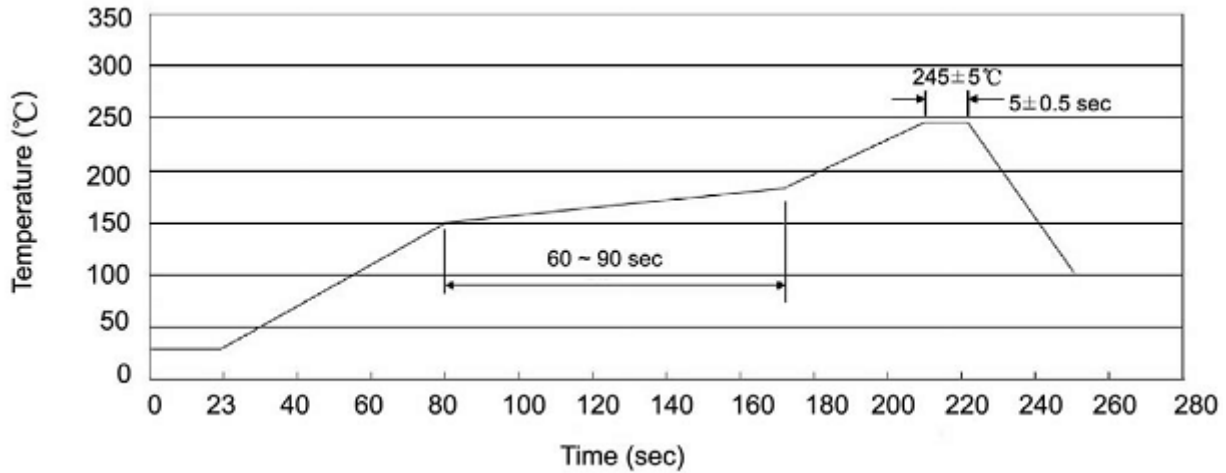
Note:

H: Company Code.

2A: Product Type.

\*\* : Lot No. Code, code change with Lot No.

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**



说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-89	1,000	7	7,000	8	56,000	7" x12	180×120×180	385×257×392

**使用说明 / Notices**